

40V NPN SMALL SIGNAL TRANSISTOR IN SOT23

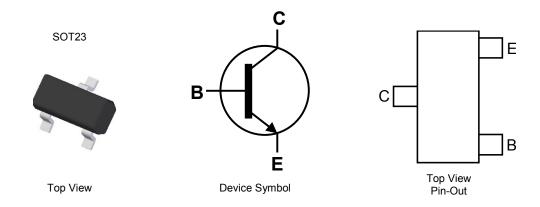
Features

- Epitaxial Planar Die Construction
- Low Saturation Voltage V_{CE(sat)} < 300mV @ 150mA
- Complementary PNP Type: MMBT2907A
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The MMBT2222AQ-7-F is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.008 grams (Approximate)



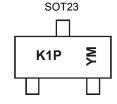
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMBT2222A-7-F	Standard	K1P	7	8	3,000
MMBT2222A-13-F	Standard	K1P	13	8	10,000
MMBT2222AQ-7-F	Automotive	K1P	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K1P = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	202	20 2	021	2022	2023	2024	2025	202	26 2	027	2028	2029
Code	Н		1	J	K	L	M	N		0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	Ο	N	D



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	Ic	600	mA
Peak Pulse Collector Current (single pulse)	I _{CM}	800	mA
Peak Pulse Base Current	I _{BM}	200	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Collector Power Dissipation	(Note 5)	D ₋	310	mW	
Collector Fower Dissipation	(Note 6)	P_{D}	350		
Thermal Resistance, Junction to Ambient	(Note 5)	В	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 8)

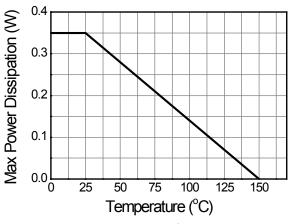
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

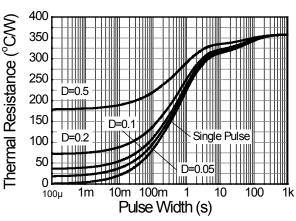
Notes

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the leads). 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



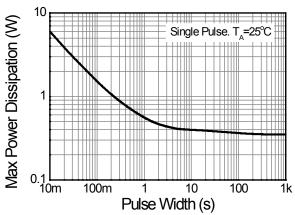
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation

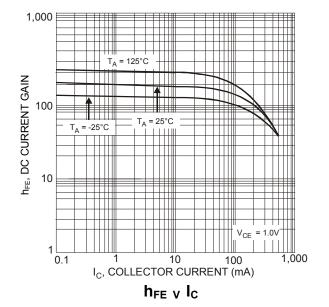


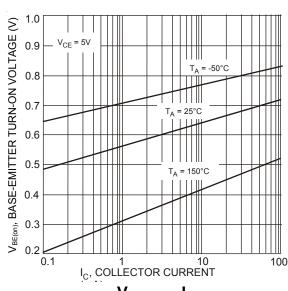
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

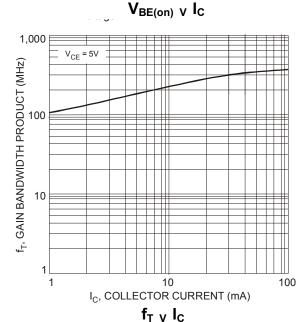
Characteristic	Symbol	Min	Max	Unit	Test Condition			
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	BV _{CBO}	75	_	V	$I_C = 100 \mu A, I_E = 0$			
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	40	_	V	$I_C = 10mA, I_B = 0$			
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	_	V	$I_E = 100 \mu A, I_C = 0$			
Collector Cut-Off Current	I _{CBO}	_	10	nΑ μΑ	$V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0, T_{A} = +150^{\circ}C$			
Collector Cut-Off Current	I _{CEX}	_	10	nA	V _{CE} = 60V, V _{EB(off)} = 3.0V			
Collector Cut-Off Current	I _{CEV}		10	nA	V _{CE} = 60V, V _{BE} = ±0.25V			
Emitter Cut-Off Current	I _{EBO}	_	10	nA	V _{EB} = 5.0V, I _C = 0			
Base Cut-Off Current	I _{BL}	_	20	nA	V _{CE} = 60V, V _{EB(off)} = 3.0V			
ON CHARACTERISTICS (Note 9)	•		•	•				
DC Current Gain	h _{FE}	35 50 75 100 40 50 35		_	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 10V \\ I_C &= 1.0 m A, \ V_{CE} = 10V \\ I_C &= 150 m A, \ V_{CE} = 10V \\ I_C &= 150 m A, \ V_{CE} = 10V \\ I_C &= 500 m A, \ V_{CE} = 10V \\ I_C &= 10 m A, \ V_{CE} = 10V, \ T_A = -55^{\circ}C \\ I_C &= 150 m A, \ V_{CE} = 1.0V \end{split}$			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.3 1.0	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA			
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.6	1.2 2.0	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA			
SMALL SIGNAL CHARACTERISTICS	•		•	•				
Output Capacitance	C _{obo}	_	8	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0			
Input Capacitance	C _{ibo}	_	25	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0			
Transition frequency	f _T	300	_	MHz	V _{CE} = 20V, I _C = 20mA, f = 100MHz			
Noise Figure	N _F	_	4.0	dB	$V_{CE} = 10V, I_{C} = 100\mu A,$ $R_{S} = 1.0k\Omega, f = 1.0kHz$			
SWITCHING CHARACTERISTICS								
Delay Time	t _d	_	10	ns	V _{CC} = 30V, I _C = 150mA, V _{BE(off)} = -0.5V, I _{B1} = 15mA			
Rise Time	t _r	_	25	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = 15mA, V _{BE(off)} = 0.5V			
Storage Time	ts	_	225	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = -I _{B2} = 15mA			
Fall Time	t _f	_	60	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = -I _{B2} = 15mA			

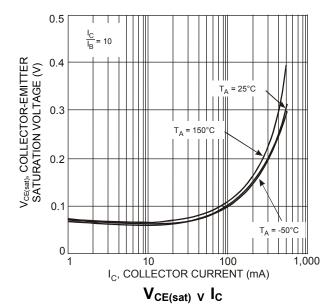
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

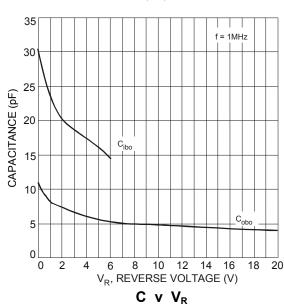


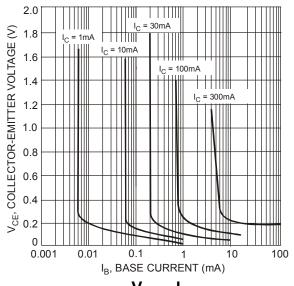










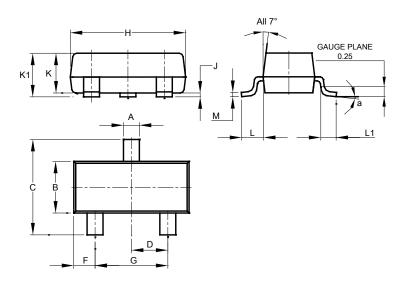




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

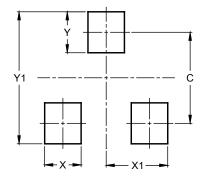


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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